

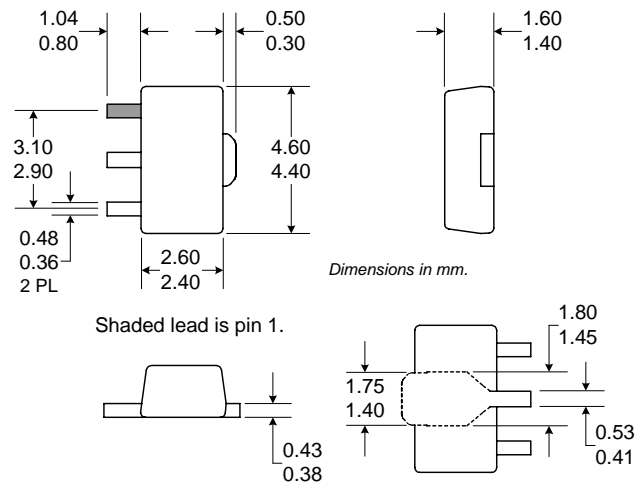
*Pb-Free Product*

### Typical Applications

- Basestation Applications
- Broadband, Low-Noise Gain Blocks
- IF or RF Buffer Amplifiers
- Driver Stage for Power Amplifiers
- Final PA for Low-Power Applications
- High Reliability Applications

### Product Description

The RF3376 is a general purpose, low-cost RF amplifier IC. The device is manufactured on an advanced Gallium Arsenide Heterojunction Bipolar Transistor (HBT) process, and has been designed for use as an easily-cascadable 50Ω gain block. Applications include IF and RF amplification in wireless voice and data communication products operating in frequency bands up to 6000MHz. The device is self-contained with 50Ω input and output impedances and requires only two external DC-biasing elements to operate as specified.



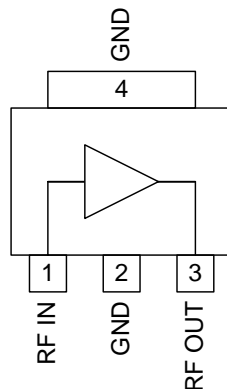
### Optimum Technology Matching® Applied

- |                                     |  |                                       |
|-------------------------------------|--|---------------------------------------|
| <input type="checkbox"/> Si BJT     | <input checked="" type="checkbox"/> GaAs HBT | <input type="checkbox"/> GaAs MESFET  |
| <input type="checkbox"/> Si Bi-CMOS | <input type="checkbox"/> SiGe HBT            | <input type="checkbox"/> Si CMOS      |
| <input type="checkbox"/> InGaP/HBT  | <input type="checkbox"/> GaN HEMT            | <input type="checkbox"/> SiGe Bi-CMOS |

### Package Style: SOT89

### Features

- DC to >6000MHz Operation
- Internally Matched Input and Output
- 22dB Small Signal Gain
- +2.0dB Noise Figure
- +11 dBm Output P1dB



**Functional Block Diagram**

### Ordering Information

RF3376 General Purpose Amplifier  
 RF3376PCBA-410 Fully Assembled Evaluation Board

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<http://www.rfmd.com>

# RF3376

## Absolute Maximum Ratings

Parameter	Rating	Unit
Input RF Power	+3	dBm
Operating Ambient Temperature	-40 to +85	°C
Storage Temperature	-60 to +150	°C
I <sub>CC</sub>	40	mA



**Caution!** ESD sensitive device.

RF Micro Devices believes the furnished information is correct and accurate at the time of this printing. However, RF Micro Devices reserves the right to make changes to its products without notice. RF Micro Devices does not assume responsibility for the use of the described product(s).

Parameter	Specification			Unit	Condition
	Min.	Typ.	Max.		
<b>Overall</b>					T=25 °C, I <sub>CC</sub> =35mA (See Note 1.)
Frequency Range		DC to >6000		MHz	
3dB Bandwidth		2		GHz	
Gain	22.0	23.5		dB	Freq=500MHz
	21.0	22.5		dB	Freq=1000MHz
	18.0	19.8		dB	Freq=2000MHz
		18.0		dB	Freq=3000MHz
		16.0		dB	Freq=4000MHz
Noise Figure		12.8			Freq=6000MHz
		2.0		dB	Freq=2000MHz
Input VSWR		<2:1			In a 50Ω system, DC to 4500MHz
Output VSWR		<2:1			In a 50Ω system, DC to 6000MHz
Output IP <sub>3</sub>	+22.0	+24.4		dBm	Freq=1000MHz
	+21.5	+23.4		dBm	Freq=2000MHz
Output P <sub>1dB</sub>	+9.5	+11.5		dBm	Freq=1000MHz
	+9.5	+11.5		dBm	Freq=2000MHz
Reverse Isolation		22.5		dB	Freq=2000MHz
<b>Thermal</b>					I <sub>CC</sub> =35mA, P <sub>DISS</sub> =110mW. (See Note 3.)
Theta <sub>JC</sub>		216		°C/W	
Maximum Measured Junction Temperature at DC Bias Conditions		109		°C	T <sub>CASE</sub> =+85°C
Mean Time To Failures		35000		years	T <sub>CASE</sub> =+85°C
<b>Power Supply</b>					With 22Ω bias resistor
Device Operating Voltage		3.4	3.5	V	At pin 8 with I <sub>CC</sub> =35mA
		4.2	4.5	v	At evaluation board connector, I <sub>CC</sub> =35mA
Operating Current		35	40	mA	See Note 2.

Note 1: All specification and characterization data has been gathered on standard FR-4 evaluation boards. These evaluation boards are not optimized for frequencies above 2.5GHz. Performance above 2.5GHz may improve if a high performance PCB is used.

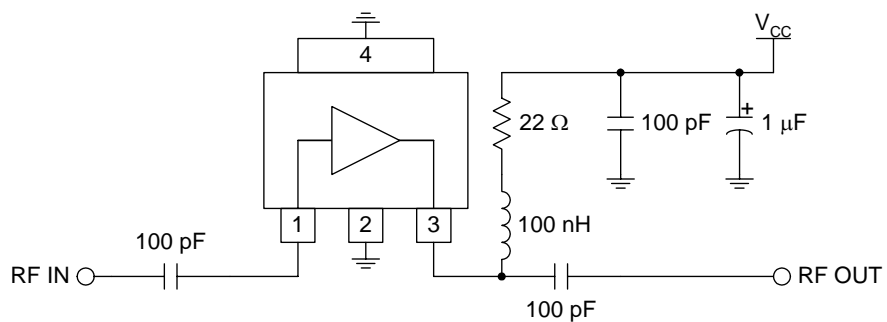
Note 2: The RF3376 must be operated at or below 40mA in order to achieve the thermal performance listed above. While the RF3376 may be operated at higher bias currents, 35mA is the recommended bias to ensure the highest possible reliability and electrical performance.

Note 3: Because of process variations from part to part, the current resulting from a fixed bias voltage will vary. As a result, caution should be used in designing fixed voltage bias circuits to ensure the worst case bias current does not exceed 40mA over all intended operating conditions.

Pin	Function	Description	Interface Schematic
1	RF IN	RF input pin. This pin is NOT internally DC blocked. A DC blocking capacitor, suitable for the frequency of operation, should be used in most applications. DC coupling of the input is not allowed, because this will override the internal feedback loop and cause temperature instability.	
2	GND	Ground connection.	
3	RF OUT	<p>RF output and bias pin. Biasing is accomplished with an external series resistor and choke inductor to <math>V_{CC}</math>. The resistor is selected to set the DC current into this pin to a desired level. The resistor value is determined by the following equation:</p> $R = \frac{(V_{SUPPLY} - V_{DEVICE})}{I_{CC}}$ <p>Care should also be taken in the resistor selection to <b>ensure that the current into the part never exceeds 40mA over the planned operating temperature</b>. This means that a resistor between the supply and this pin is always required, even if a supply near 3.4V is available, to provide DC feedback to prevent thermal runaway. Because DC is present on this pin, a DC blocking capacitor, suitable for the frequency of operation, should be used in most applications. The supply side of the bias network should also be well bypassed.</p>	
4	GND	Ground connection.	

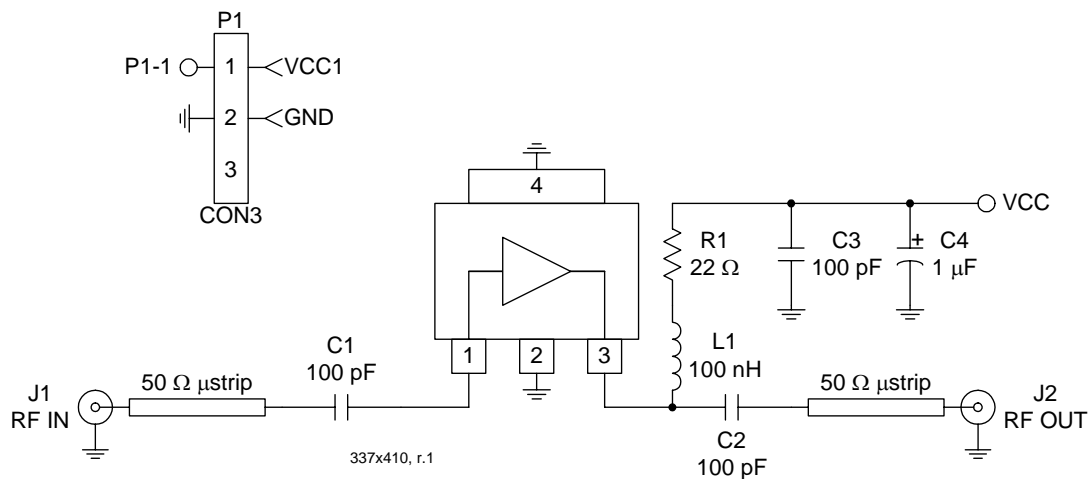
# RF3376

## Application Schematic



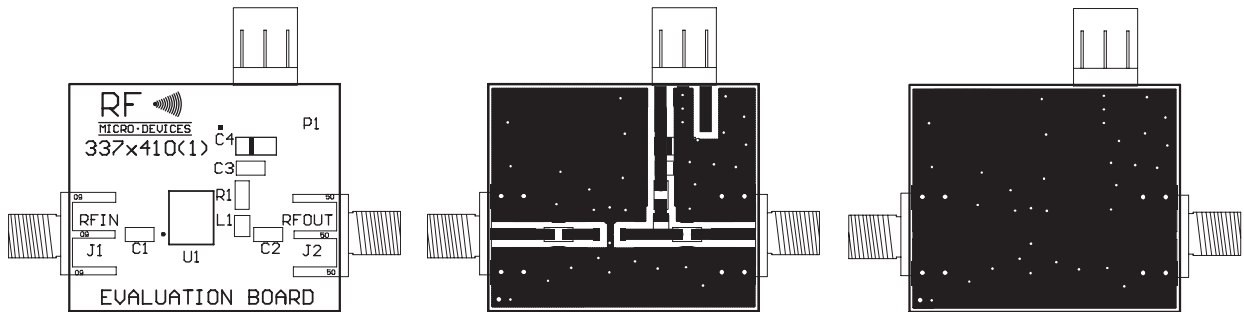
## Evaluation Board Schematic

(Download [Bill of Materials](http://www.rfmd.com) from [www.rfmd.com](http://www.rfmd.com).)



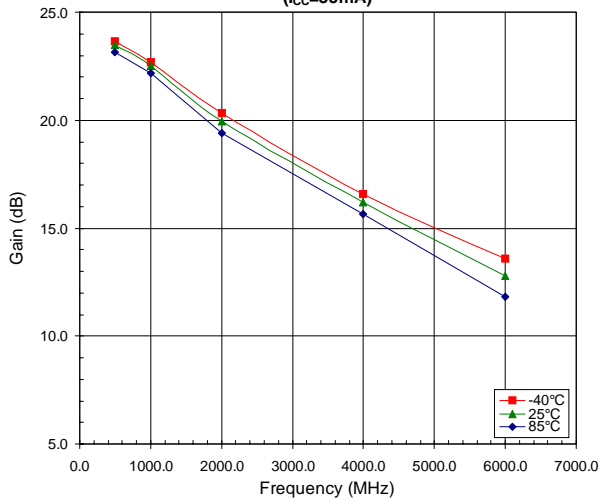
### Evaluation Board Layout Board Size 1.195" x 1.000"

Board Thickness 0.033", Board Material FR-4

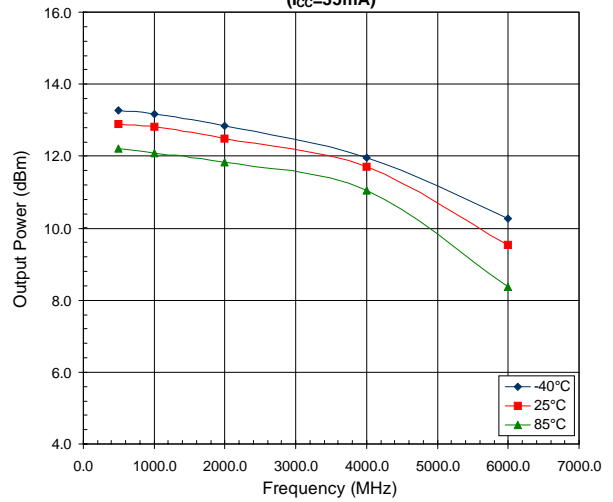


# RF3376

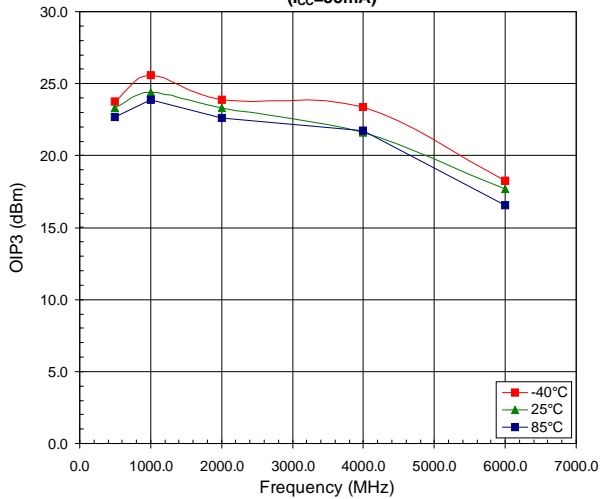
**Gain versus Frequency Across Temperature**  
( $I_{CC}=35mA$ )



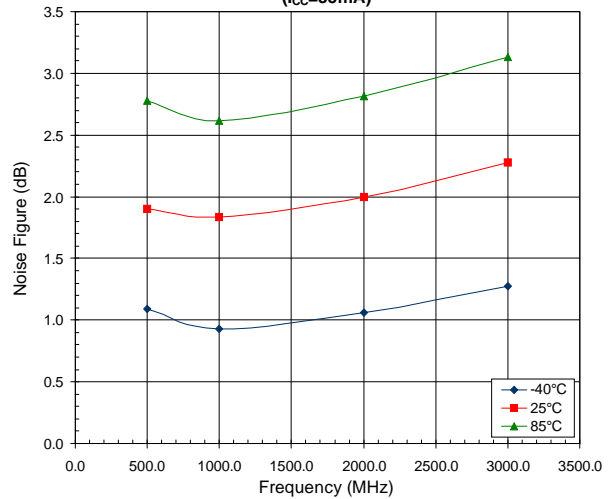
**Output P1dB versus Frequency Across Temperature**  
( $I_{CC}=35mA$ )



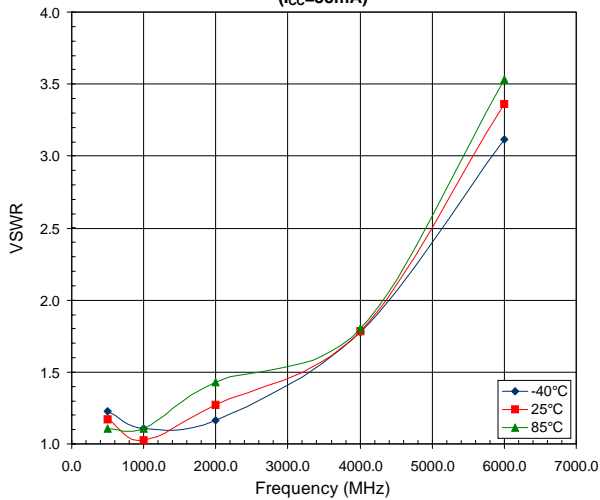
**Output IP3 versus Frequency Across Temperature**  
( $I_{CC}=35mA$ )



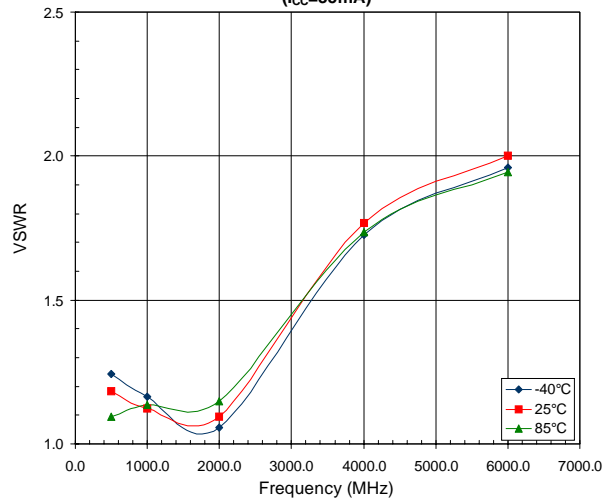
**Noise Figure versus Frequency Across Temperature**  
( $I_{CC}=35mA$ )



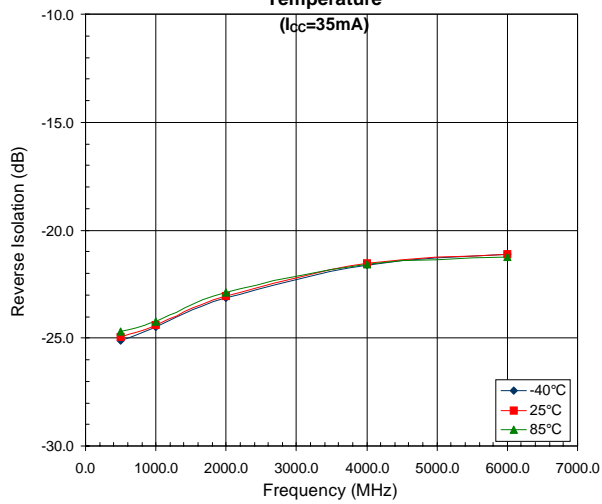
**Input VSWR versus Frequency Across Temperature**  
( $I_{CC}=35mA$ )



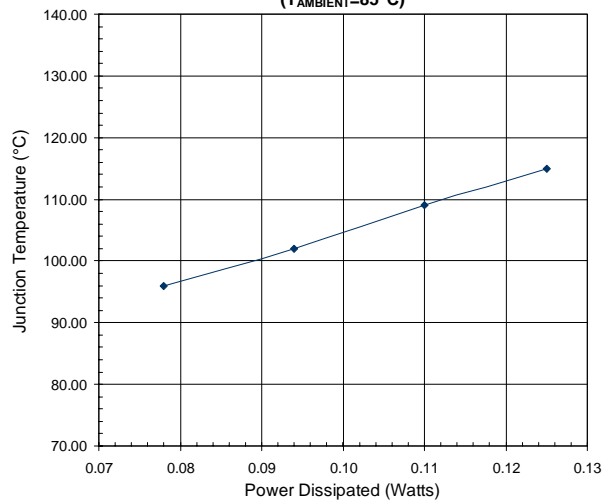
**Output VSWR versus Frequency Across Temperature**  
( $I_{CC}=35mA$ )



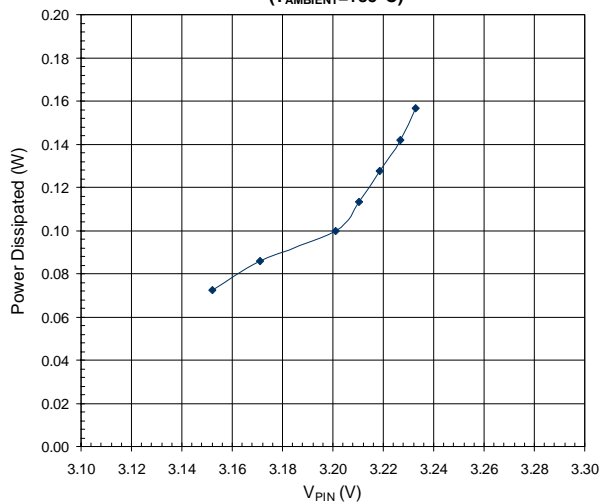
**Reverse Isolation versus Frequency Across Temperature**  
( $I_{DC}=35\text{mA}$ )



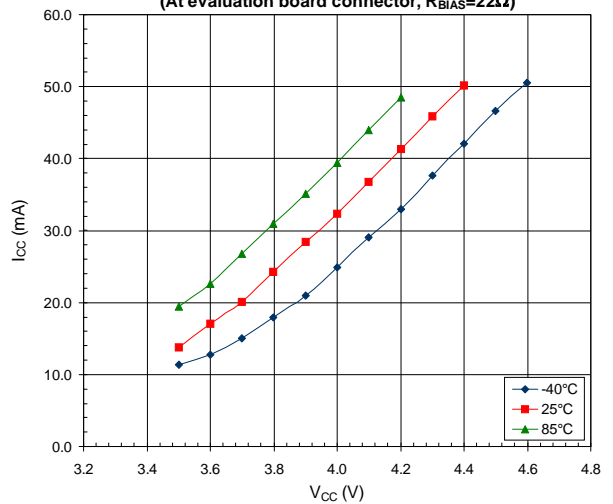
**Junction Temperature versus Power Dissipated**  
( $T_{\text{AMBIENT}}=85^\circ\text{C}$ )



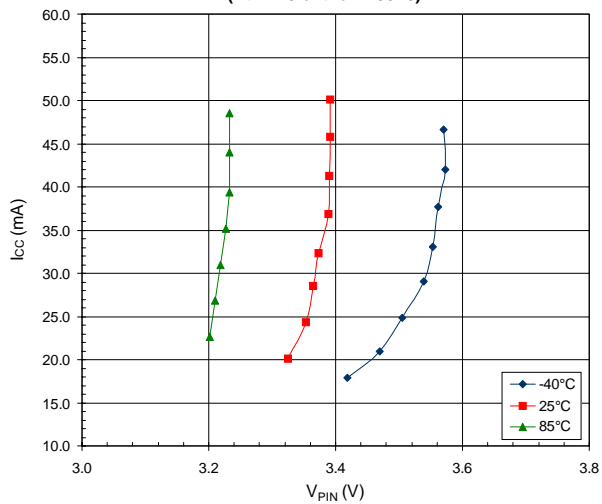
**Power Dissipation versus Device Voltage Across Temperature**  
( $T_{\text{AMBIENT}}=+85^\circ\text{C}$ )



**Bias Current versus Supply Voltage Across Temperature**  
(At evaluation board connector,  $R_{\text{BIAS}}=22\Omega$ )



**Bias Current versus Devices Voltage Across Temperature**  
(At Pin 3 of the RF3376)



**RF3376**